

### LP1PP06CXXP01 Series

### **Electrostatic Discharged Protection Devices**

Datasheet-production date

### **Descriptions**

The LP1PP06CXXP01 series are designed to protect sensitive electronics from damage or latch-up due to ESD. They are designed to replace 0201 size multilayer varistors (MLVs) in portable applications such as cell phones,notebook computers, and other portable electronics. It features large cross-sectional area junctions for conducting high transient currents. This device offers desirable characteristics for board level protection including fast response time, low operating and clamping voltage, and no device degradation.

LP1PP06CXXP01 series features extremely good ESD protection characteristics highlighted by low typical dynamic resistance, low peak ESD clamping voltage, and high ESD withstand voltage (+/-15kV contact per IEC 61000-4-2). Low maximum capacitance (5pF at V<sub>R</sub>=0V) minimizes loading on sensitive cirucuits. Each device will protect one data.LP1PP0603CXXP01 measures 0.6 x 0.3 mm with a nominal height of only 0.25mm. The small package gives the designer the flexibility to protect single lines in applications where arrays are not practical. The combination of small size and high ESD surge capability makes them ideal for use in portable applications such as cellular phones, digital cameras, and tablet PC's.

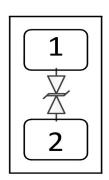
#### **Features**

- ♦ High ESD withstand Voltage: +/-15kV (Contact) and +/- 17kV (Air) per IEC 61000-4-2
- ♦ Ultra-small package
- Protects one data line
- ♦ Low ESD clamping voltage
- ♦ Working voltage: 3.3V/5V
- ♦ Low capacitance: 15pF Maximum
- ♦ Lower leakage current
- Solid-state silicon-avalanche technology
- ♦ Pb-Free, Halogen Free, RoHS/WEEE compliant
- ♦ Nominal Dimensions: 0.6 x 0.3 x 0.25 mm
- Marking code:f
- Packaging: Tape and Reel

## **Applications**

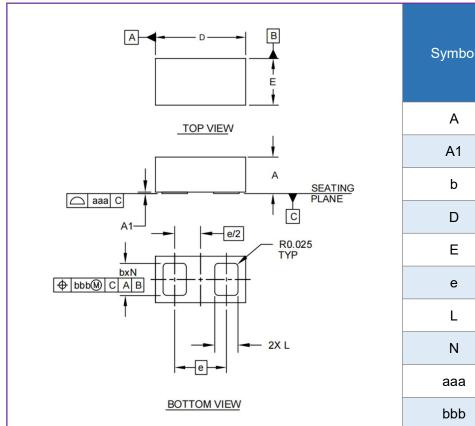
- Cellular Handsets & Accessories
- Peripherals
- Portable Instrumentation
- Notebook Computers
- Tablet PC

#### **Schematic**





# **Dimension(SLP0603P2X3F Unit:mm)**



	Dimension			
Symbol	Millimeters			
	Min.	Max.		
А	0.235	0.265		
A1	0.000	0.050		
b	0.200	0.240		
D	0.580	0.620		
E	0.280	0.320		
е	0.355 BSC			
L	0.140	0.180		
N	2			
aaa	0.08			
bbb	0.10			

# Maximum Rating and Characteristics at 25℃ ambient temperature unless otherwise Noted.

Rating	Symbol	Value	Unit	
ESD per IEC 61000-4-2 (Air )	V	±17	kV	
ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	±15		
Operating Temperature	Тл	-40 to +125	${\mathbb C}$	
Storage Temperature	T <sub>STG</sub>	-55 to +150	$^{\circ}$ C	

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# **Electrical Characteristics (T<sub>A</sub>=25** <sup>°</sup>C unless otherwise noted)

#### LP1PP06C3.3P01

Parameter	Symbol	Conditions	Mini mum	Typical	Maximum	Unit
Peak Pulse Current	I <sub>PP</sub>	tp = 8/20µs			4	Α
Peak Pulse Power	P <sub>PP</sub>	tp = 8/20μs		40		W
Reverse Stand-Off Voltage	V <sub>RWM</sub>	Pin 1 to 2 or Pin 2 to 1			3.3	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> =50μA Pin 1 to 2 or Pin 2 to 1	3.7	4.0	4.7	V
Reverse Leakage	I <sub>R</sub>	V <sub>RWM</sub> =3.3V Pin 1 to 2 or Pin 2 to 1		1	50	μΑ
Clamping Voltage	Vc	I <sub>PP</sub> =4A,t <sub>p</sub> =8/20μs			8.5	V
ESD Clamping Voltage	V	I <sub>PP</sub> =4A,t <sub>p</sub> =0.2/100ns		6.5		V
	Vc	I <sub>PP</sub> =16A,t <sub>p</sub> =0.2/100ns		10.5		V
Junction Capacitance	Сл	V <sub>R</sub> =0V,f=1MHz I/O pin to GND		12	15	pF



# **Electrical Characteristics (T<sub>A</sub>=25** <sup>°</sup>C unless otherwise noted)

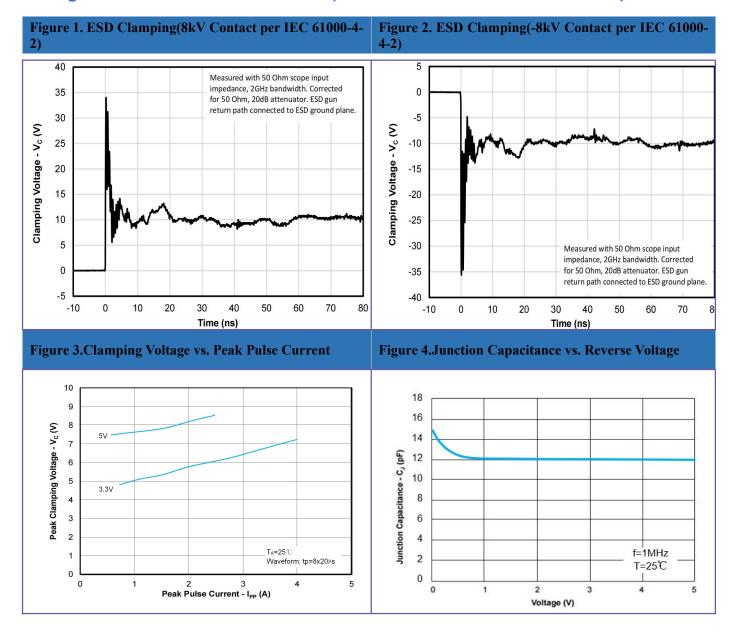
#### LP1PP06C05P01

Parameter	Symbol	Conditions	Mini mum	Typical	Maximum	Unit
Peak Pulse Current	Ірр	tp = 8/20µs			2.5	Α
Peak Pulse Power	P <sub>PP</sub>	tp = 8/20µs		30		W
Reverse Stand-Off Voltage	V <sub>RWM</sub>	Pin 1 to 2 or Pin 2 to 1			5	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> =1mA Pin 1 to 2 or Pin 2 to 1	6.5	8.5	10.5	V
Reverse Leakage	I <sub>R</sub>	V <sub>RWM</sub> =5V Pin 1 to 2 or Pin2 to 1		5	20	μΑ
Clamping Voltage	Vc	I <sub>PP</sub> =2.5A,t <sub>p</sub> =8/20μs			12	V
ESD Clamping Voltage	V	I <sub>PP</sub> =4A,t <sub>p</sub> =0.2/100ns		8		V
	Vc	I <sub>PP</sub> =16A,t <sub>p</sub> =0.2/100ns		9.8		V
Junction Capacitance	Сл	V <sub>R</sub> =0V,f=1MHz I/O pin to GND		12	15	pF

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## Ratings and Characteristic Curves (T<sub>A</sub>=25 ℃ unless otherwise noted)



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### **Reflow Soldering Parameters**

